



MMBT2222ATB

NPN GENERAL PURPOSE SWITCHING TRANSISTOR

VOLTAGE 40 Volts

POWER 225 mWatts

SOT-523

Unit: inch (mm)

FEATURES

- NPN epitaxial silicon, planar design
- Collector-emitter voltage $V_{CE} = 40V$
- Collector current $I_C = 600mA$
- In compliance with EU RoHS 2002/95/EC directives

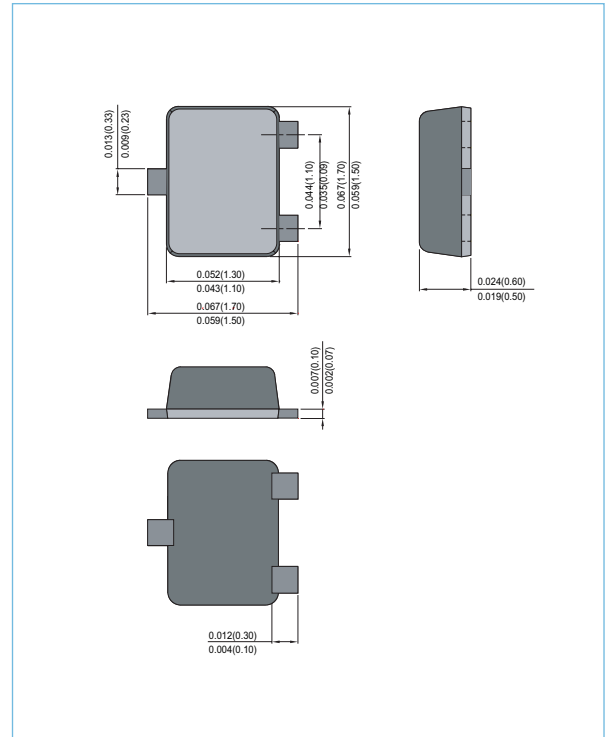
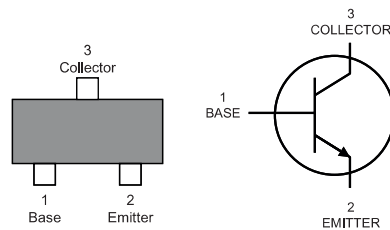
MECHANICAL DATA

Case: SOT-523, Plastic

Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.002 gram

Marking: MY



ABSOLUTE RATINGS

PARAMETER	Symbol	Value	Units
Collector - Emitter Voltage	V_{CE0}	40	V
Collector - Base Voltage	V_{CBO}	75	V
Emitter - Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	600	mA

THERMAL CHARACTERISTICS

PARAMETER	Symbol	Value	Units
Max Power Dissipation (Note 1)	P_{TOT}	225	mW
Thermal Resistance , Junction to Ambient	$R_{\theta JA}$	833	$^{\circ}C/W$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^{\circ}C$

Note 1: Transistor mounted on FR-5 board 1.0 x 0.75 x 0.062 in.



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ELECTRICAL CHARACTERISTICS

PARAMETER	Symbol	Test Condition	MIN.	TYP.	MAX.	Units
Collector - Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1.0mA, I_B=0$	40	-	-	V
Collector - Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	75	-	-	V
Emitter - Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6.0	-	-	V
Base Cutoff Current	I_{BL}	$V_{CE}=60V, V_{EB}=3.0V$	-	-	20	nA
Collector Cutoff Current	I_{CEX}	$V_{CE}=60V, V_{EB}=3.0V$	-	-	10	nA
	I_{CBO}	$V_{CE}=60V, I_E=0,$ $V_{CE}=60V, I_E=0, T_J=125^\circ C$	-	-	10 10	nA uA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=3.0V, I_C=0,$	-	-	100	nA
DC Current Gain	h_{FE}	$I_C=0.1mA, V_{CE}=10V$	35	-	-	-
		$I_C=1.0mA, V_{CE}=10V$	50	-	-	
		$I_C=10mA, V_{CE}=10V$	75	-	-	
		$I_C=10mA, V_{CE}=10V, T_J=125^\circ C$	35	-	-	
		$I_C=150mA, V_{CE}=10V$ (Note 2)	100	-	300	
Collector - Emitter Saturation Voltage (Note 2)	$V_{CE(SAT)}$	$I_C=150mA, I_B=15mA$	-	-	0.3	V
		$I_C=500mA, I_B=50mA$	-	-	1.0	
Base - Emitter Saturation Voltage (Note 2)	$V_{BE(SAT)}$	$I_C=150mA, I_B=15mA$	0.6	-	1.2	V
		$I_C=500mA, I_B=50mA$	-	-	2.0	
Collector - Base Capacitance	C_{CBO}	$V_{CB}=10V, I_E=0, f=1MHz$	-	-	8.0	pF
Emitter - Base Capacitance	C_{EBO}	$V_{CB}=0.5V, I_C=0, f=1MHz$	-	-	25	pF
Delay Time	t_d	$V_{CC}=3V, V_{BE}=-5V,$ $I_C=150mA, I_B=15mA$	-	-	10	ns
Rise Time	t_r	$V_{CC}=3V, V_{BE}=-5V,$ $I_C=150mA, I_B=15mA$	-	-	25	ns
Storage Time	t_s	$V_{CC}=30V, I_C=150mA$ $I_{B1}=I_{B2}=15mA$	-	-	225	ns
Fall Time	t_f	$V_{CC}=30V, I_C=150mA$ $I_{B1}=I_{B2}=15mA$	-	-	60	ns

Note 2: Pulse Test: Pulse Width ≤ 300 us, Duty Cycle $\leq 2.0\%$.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

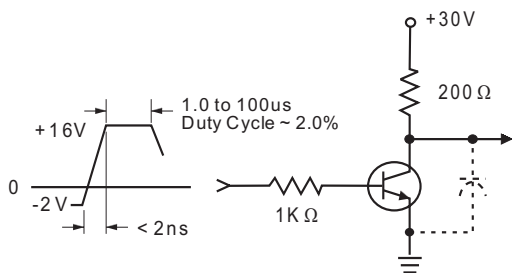


Fig. 1 Turn-On Time

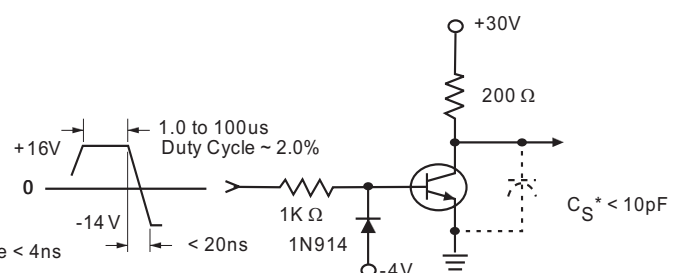


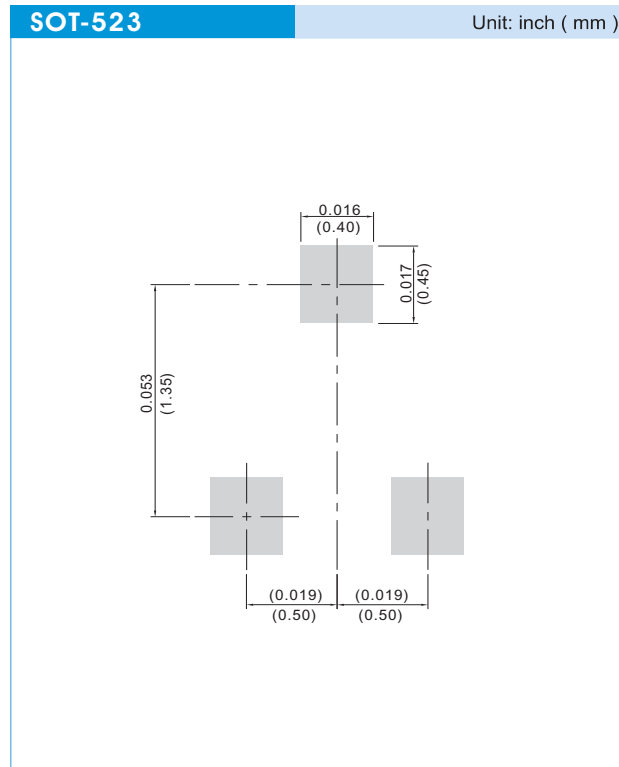
Fig. 2 Turn-Off Time

* Total shunt capacitance of test jig, connectors, and oscilloscope



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MOUNTING PAD LAYOUT



ORDER INFORMATION

- Packing information

T/R - 3K per 7" plastic Reel

T/R - 10K per 13" plastic Reel

LEGAL STATEMENT

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